Two-Dimensional Spintronic Circuit Architectures on Large Scale Graphene

Dmitrii Khokhriakov¹, Bogdan Karpiak¹, Anamul Md. Hoque¹, Saroj P. Dash

¹Department of Microtechnology and Nanoscience, Chalmers University of Technology, SE-41296, Göteborg, Sweden

Abstract

Solid state electronics based on utilizing the electron spin degree of freedom for storing and processing information can pave the way for next-generation spin-based computing. However, the realization of spin communication between multiple devices in complex spin circuit geometries, essential for practical applications, is still lacking. Here we demonstrate the spin current propagation in two-dimensional (2D) circuit architectures consisting of multiple devices and configurations using a large area CVD graphene on SiO₂/Si substrate at room temperature. Taking advantage of the breakthrough spin transport distance reaching 33 μm in commercially available wafer-scale graphene grown on Cu foil, we demonstrate that the spin current can be effectively communicated between the magnetic memory elements in graphene channels with different 2D circuits of Y-junction and hexa-arm architectures. We further show that by designing graphene channels and ferromagnetic elements at different geometrical angles, the symmetric and antisymmetric components of the Hanle spin precession signal can be remarkably controlled. These findings lay the foundation for the design of efficient pure-spin-current-based electronics, which can be integrated into complex two-dimensional spintronic circuits.

Keywords: graphene, spin circuit, spin device architecture, spin transport, Hanle spin precession.

Corresponding authors: Dmitrii Khokhriakov, Email: dmikho@chalmers.se; Saroj P. Dash, Email: saroj.dash@chalmers.se
Main

The utilization of spin degree of freedom as a state variable for information processing and storage is expected to allow faster device operation and lower power consumption, promising for applications in spintronics, artificial intelligence, and quantum technology\textsuperscript{1,2}. For the realization of hybrid spin-based logic and memory technologies such as spin transistors and all-spin-logic devices, one needs to develop spin circuit designs combining different spintronic concepts such as efficient spin injection, detection and long-distance spin transport in nonmagnetic channels with magnetization dynamics of nanomagnets\textsuperscript{3–8}. Such spin circuits should be composed of multiple nanomagnetic elements interconnected with spin-coherent channel materials. In the last decade, the search for a spin interconnect material exhibiting long spin lifetime and spin diffusion length at room temperature is intensified with the investigation of spin transport in metals\textsuperscript{9}, semiconductors\textsuperscript{10–13}, topological materials\textsuperscript{14} and graphene\textsuperscript{15–19}.

The concept of using graphene as interconnect for spin-polarized electrons comes naturally because of the outstanding electrical, mechanical and thermal properties, while its two-dimensional (2D) nature allows for large current densities. Most importantly, graphene is an excellent candidate for long-distance spin interconnect due to the low spin-orbit coupling and lack of hyperfine interaction in carbon, and its high electron mobility\textsuperscript{15–19}. Spin transport properties with more than 10 nanosecond spin lifetime and 25 μm spin transport distance are demonstrated in h-BN encapsulated single crystals of exfoliated graphene samples at room temperature\textsuperscript{20,21}. Recently, using chemical vapor deposited (CVD) graphene, very long distance spin transport with comparable spin transport parameters was demonstrated\textsuperscript{22–24}. In addition to the perspective spin interconnect functionality of graphene, it may be also possible to produce heterostructure-based active spintronic devices with creation and control of spin polarization\textsuperscript{25–29}. Despite these developments, so far, the spin transport studies in graphene are limited to a simple straight graphene stripe, and demonstration of spin circuits in complicated device geometries as required for spintronic memory and logic applications remained challenging.

Here, we demonstrate spin circuit architectures with large area graphene channels efficiently carrying and communicating the spin information between nanomagnets arranged in different complex geometries consisting of multiple devices. We take advantage of extraordinary long-distance spin transport observed in commercially available wafer scale CVD graphene samples with transport lengths exceeding 33 μm at room temperature. The advantage of making spin circuits on graphene produced by a CVD method on Cu foil is the possibility to produce high-quality spintronic devices at low cost. Utilizing our optimized nanofabrication and patterning techniques compatible with industrial manufacturing processes, we carved complicated graphene Y-junction and hexa-arm spin circuit architectures. This experimental demonstration of graphene spin circuit functionality is a milestone towards large-scale integration and development of spin-logic technologies.
Figure 1. The 2D graphene spintronic circuit. 

a. An artistic representation of a graphene spin circuit composed of multiple nanomagnetic elements interconnected with graphene channels. The functionality of the circuit includes spin injection, transport, detection in graphene and magnetization dynamics of the nanomagnets. 

b. The nanofabricated spin circuit (a hexa-arm architecture) on a chip (7x7 mm²) picked from a 4-inch CVD graphene wafer on SiO₂/Si substrate. The circuit shows the patterned CVD graphene channels with ferromagnetic TiO₂/Co (yellow) tunnel contacts and non-magnetic Ti/Au (orange) reference contacts defined by electron beam lithography. The ferromagnetic elements are used for injection and detection of spin-polarized current in the graphene circuit.

Large scale CVD graphene spin circuits

Schematic of a spin circuit composed of nanomagnetic elements interconnected with graphene channels is shown in Fig. 1a. The functionality of the circuit includes spintronic phenomena such
as spin injection, transport, detection, precession, and magnetization switching processes. The CVD graphene spin circuit is prepared from a chip picked from a 4-inch wafer completely covered with graphene grown on Cu foil (from Grolltex Inc.) and subsequently transferred on a SiO₂/Si substrate. Figure 1b shows the pictures of the graphene-covered wafer, the chip with nanofabricated spin circuits and a representative hexa-arm device. The patterning of graphene circuit and preparation of ferromagnetic and non-magnetic contacts were done by multi-step electron beam lithography process. The final circuit consists of graphene channels in different geometries with ferromagnetic Co/TiO₂ contacts as the injector and detector electrodes for spin-polarized current, Ti/Au electrodes as reference contacts, while the n⁺⁺Si/SiO₂ is used as a global back gate (see Methods for details of the nanofabrication process). In the spin circuits, the graphene channels with lengths up to 26.6 μm and the ferromagnetic contacts having different widths between 200–400 nm were prepared. The ferromagnetic tunnel contact resistances (R₀) measured in the three-terminal configuration were around 2–10 kΩ, while the graphene channel resistance was measured to be R₀ = 1–5 kΩ/μm with field-effect mobility μ = 1000–2000 cm²V⁻¹s⁻¹ at room temperature (see Supplementary Figure S1a). The quality of the graphene channel was verified by the Raman spectroscopy as shown in Supplementary Figure S1b.

Spin transport in CVD graphene Y-junction circuit

First, spin transport properties of the CVD graphene were investigated in a Y-junction circuit with channel length up to 26.6 μm at room temperature. Figures 2a,b show the optical microscopy picture and schematics of the device with the measurement geometry used to determine the spin transport parameters of the large area CVD graphene. The spin accumulation is created by passing a constant DC current (I) in the injector ferromagnetic contact, while the nonlocal (NL) pure spin transport voltage signal (VNL) is detected by another ferromagnetic contact placed at a length L away from the injector on the graphene channel. This nonlocal spin injection and detection in lateral graphene spintronic devices is an effective method to generate a pure spin current for potential spintronic applications. We perform two kinds of spin-sensitive NL measurements in our CVD graphene spin circuits with different channel lengths and geometries: spin valve and Hanle spin precession measurements. The spin valve data give an estimate of the magnitude of induced spin polarization, while Hanle spin precession curves allow to extract parameters such as spin lifetime τₛ, spin diffusion coefficient Dₛ and spin diffusion length λₛ in graphene.

Figures 2c and 2d show the measured spin valve and Hanle spin precession data in the nonlocal (NL) configuration in channels of different lengths (6.6, 20, 26.6 μm) and geometries in the graphene Y-junction. In this circuit, the ferromagnetic injector and detector contacts are placed parallel to each other. To perform the spin valve measurement, we sweep the in-plane magnetic field (Bǁ) along the easy axis of the ferromagnetic contacts while recording the nonlocal resistance (Rₓ = Vₓ/I). The sharp changes in Rₓ are measured when the magnetization of the injector or detector switches to either parallel or antiparallel configuration. The in-plane external magnetic field switches the magnetization of the ferromagnetic electrodes at their respective coercive fields, which are defined by their widths. Figure 2c shows the change in ΔRₓ from ~0.4 Ω in L = 6.6 μm
Figure 2. Graphene Y-junction spin circuit. a-b. Optical microscope image and schematic of a fabricated CVD graphene device in a Y-junction spin circuit having spin transport channel lengths $L = 6.6, 20$ and $26.6 \mu m$ with multiple ferromagnetic Co/TiO$_2$ (yellow) injector/detector and non-magnetic Au/Ti (orange) reference contacts. The NL measurement scheme is shown with current ($I$) and voltage ($V$) circuits. The first geometry (between contacts 2 and 3) is a conventional longitudinal channel, whereas the other two
channels are in a Y-junction circuit. c. NL spin valve signal for different graphene channel lengths with in-plane magnetic field (B) sweep. d. Hanle spin precession signals $R_{NL}$ measured with a perpendicular magnetic field ($B_\perp$) sweep. The data shown for $L = 20$ and 26.6 μm are obtained by averaging the Hanle signals in parallel (↑↑) and antiparallel (↑↓) configuration of ferromagnetic electrodes as $R_{NL} = \frac{R_{NL}^{\uparrow\uparrow} - R_{NL}^{\uparrow\downarrow}}{2}$. The data points are fitted with the Hanle equation to extract spin lifetime $\tau_s$ and spin diffusion constant $D_s$. e. Channel length dependence of the spin valve magnitude. For channels having a bifurcation (20 and 26.6 μm), the magnitude is doubled to compensate for the part of the spin accumulation that was transferred to another graphene branch. The arrow shows the estimated maximum spin transport distance found at the intersection of the fit to an exponential decrease of spin valve amplitude with distance (red line) and the noise level of the measurements (shaded area). The untreated data are also shown for comparison. f-g. Channel length dependence of spin lifetime $\tau_s$ and spin diffusion length $\lambda_s$ extracted from Hanle spin precession measurements.

to 0.8 mΩ in $L = 26.6$ μm graphene channel lengths at room temperature. This data can be used to evaluate the spin diffusion length of graphene using the exponential decay of spin signal with distance, $R_{NL} \propto e^{-L/\lambda_s}$. However, we note that the channels with $L = 20$ and 26.6 μm in the Y-junction have an additional graphene channel branching off between injector and detector contacts. This is expected to reduce the observed spin signal magnitude by a factor of two compared to the channel without branches. Therefore, to extract the intrinsic graphene property, we double these amplitudes for the fitting, as shown in Fig 2e. Considering this, we extract the spin diffusion length $\lambda_s = 3.9$ μm. The data without amplitude doubling are also shown for comparison, yielding $\lambda_s = 3.4$ μm. We estimate the maximum detectable spin transport distance in our graphene circuit to be 33.7 μm by extrapolating the fit to the noise level of our measurements, as shown in Fig 2e. In addition, we note here that the 26.6 μm (20 μm) channel has two (one) ferromagnetic contacts on top of the channel between injector and detector, which can further reduce the spin signal due to spin absorption. This indicates that the obtained spin parameters are a lower bound estimation, and optimizations in the device design and fabrication process can yield even longer spin transport distances.

Hanle spin precession measurements, in contrast to the spin valve, can be used to extract spin diffusion length and other parameters of the system from a single measurement. They are performed by measuring the NL resistance $R_{NL}$ while applying an out-of-plane magnetic field ($B_\perp$), which induces spin precession with the Larmor frequency resulting in dephasing of the spin polarization, as shown in Figure 2d. The data are fitted with eq.1,

$$\Delta R_{NL} \propto \int_0^\infty \frac{1}{\sqrt{4\pi D_s t}} e^{-\frac{t^2}{4D_s}} \cos(\omega_L t) e^{-\left(\frac{t}{\tau_s}\right)} dt,$$

where $\omega_L = \frac{g\mu_BB_\perp}{\hbar}$ is the Larmor spin precession frequency, $\mu_B$ is Bohr magneton, $L$ is the channel length, $D_s$ the spin diffusion coefficient and $\tau_s$ spin lifetime. For the channel length of $L = 26.6$ μm, we extract the spin lifetime $\tau_s = 424$ ps, spin diffusion constant $D_s = 0.036 m^2s^{-1}$ and the spin diffusion length $\lambda_s = 3.9$ μm. The estimated $\tau_s$ and $\lambda_s$ for different graphene channel length are shown in Fig. 2f-g. The spin diffusion length obtained from the Hanle measurement...
data $\lambda_s = 3.2$–$3.9$ $\mu$m matches well with the $\lambda_s = 3.9$ $\mu$m extracted from the channel length dependence of the spin valve magnitude. Similar spin parameters for different channel lengths indicate that contact-induced spin relaxation is not a major source of spin scattering in our devices. Both the spin valve and Hanle measurements establish that the spin current in CVD graphene can propagate to a channel length of 26.6 $\mu$m at room temperature and we estimate that spin signal should be detectable in channels even longer than 33 $\mu$m. This spin transport distance is the highest achieved so far at room temperature in CVD graphene grown on Cu foil and transferred on a 4-inch Si/SiO$_2$ wafer, which opens the possibility to produce high-quality spintronic devices at low cost. To be noted, after the preparation of this manuscript, we came across a recent publication where a comparable spin transport distance is reported in CVD graphene grown on a Pt foil$^{32}$. Our results on the Y-junction graphene spin circuit can be implemented in a spin summation gate, where the spin polarization on both inputs contributes to the total spin density at the output. The spin voltage at the detector would be maximum when both injectors and the detector magnetizations are parallel, minimum when both injectors are parallel to each other and antiparallel to the detector, and zero if the two injectors are antiparallel to each other. In addition, graphene Y-junctions are proposed for spin demultiplexing applications controlled by drift current$^8$.

**Spin circuit with a graphene hexa-arm architecture**

To exploit the excellent spin transport properties of the CVD graphene, we further investigated spin transport and precession in a more complex graphene spin circuit with a hexa-arm geometry, as shown in Figures 3a, b. Figure 3c shows the NL spin valve measurements in a channel having a 60° angle between the graphene branches, where the ferromagnetic injector and detector contacts are placed perpendicularly to each corresponding branch. It should be noted that the measured spin valve signal is merely one-fifth of the total spin accumulation created by the injector because of the expected isotropic diffusion of spin current to the other four branches in the spin circuit. Moreover, due to the non-collinearity between the injector and detector contact magnetizations, the measured spin valve signal amplitude shows only the projected component of the spin polarization in the channel on the detector magnetization. To account for the total spin density in graphene, we employ Hanle spin precession experiments as shown in Figure 3d. Since the injected spins are rotated at an angle of 60° with respect to the detector, an asymmetric Hanle is observed. The Hanle spin precession signal is measured for both "parallel" and "antiparallel" alignment of the ferromagnetic injector and detector electrodes, which is defined by the positive or negative projection of the injector magnetization on the detector. The results are consistent with the expected behavior of a spin current polarization rotated at 60° with respect to the magnetization direction of the detector. We deconvolute both signals to the symmetric and antisymmetric components as shown in Fig. 3e-f, which correspond to the parallel (∥) and perpendicular (⊥) components of injected spin polarization projected on the detector. The curves are simultaneously fit with equation (1) containing $\cos(\omega_L t)$ for the parallel component and $\sin(\omega_L t)$ for the perpendicular component. The extracted amplitudes of the components allow us to back-calculate the relative angle between injector and detector contacts as $\theta' = \tan^{-1}\left(\frac{\Delta R_{NL}^\perp}{\Delta R_{NL}^\parallel}\right)$. For the angular convention shown in figure 4c the signs of $\Delta R_{NL}^\perp$ and $\Delta R_{NL}^\parallel$ can
Figure 3. Graphene hexa-arm spin circuit architecture. a. Optical microscopy image of a fabricated CVD graphene device in a hexa-arm junction having multiple ferromagnetic tunnel contacts of Co/TiO$_2$ with the channel length between inner electrodes of $L = 7.8 \ \text{μm}$. b. A schematic of the hexa-arm channel with 60° angle between graphene branches and the injector/detector contacts placed perpendicularly to the respective graphene channels. c. NL spin valve signal for the measurement configuration highlighted in (b) with in-plane magnetic field ($B_i$) sweep. d. Asymmetric NL Hanle spin precession signal obtained by a perpendicular magnetic field ($B_i$) sweep in “parallel” and “antiparallel” configurations of ferromagnetic electrodes at room temperature. e-f. Hanle signals deconvoluted into the symmetric and antisymmetric components with fits to eq. 1.


be taken into consideration to obtain the absolute angle in degrees via $\theta = \theta' + 90° \cdot \text{sign}(\Delta R_{NL}) \cdot [1 - \text{sign}(\Delta R_{NL}^I)]$. The sign of the parallel component is taken as positive when the projection of injector magnetization on detector points in the same direction as the magnetization of the detector. For the perpendicular component, the sign is assumed positive when the projection of the injector magnetization on the orthogonal direction to the detector magnetization is pointing 90° counterclockwise to the detector magnetization. The extracted angles of 60.1° for “parallel” and -123° for “antiparallel” configurations correspond well to the geometry of the device, proving the validity of the method. Note that the extracted amplitude of the symmetric Hanle component ($|\Delta R_{NL}^I| = 1.9–2.6 \ \text{mΩ}$) is in agreement with the spin valve amplitude (Fig. 3c), showing that spin valve is only sensitive to the component of the spin polarization parallel to the detector magnetization.$^{33}$
Having observed and analyzed the asymmetric Hanle spin precession within one pair of injector/detector contacts, we performed experiments in a distributed spin-circuit geometry where the spin injected in one contact is measured with detectors in different graphene branches simultaneously. Figure 4a shows the schematic of different channel geometries used for Hanle spin precession measurements with graphene branches being oriented at angles of 60°, 120° and 0° to each other, respectively. Figure 4b shows the measured Hanle curves, having a conventional symmetric shape for the straight channel and asymmetric shapes for electrodes oriented at 60° and 120°. The deconvoluted symmetric and antisymmetric Hanle components for each geometry are shown in their corresponding panels. Using the contact 1 for the spin injection and contacts 2 and 3 simultaneously for the spin detection, we measure Hanle signals of different shapes and magnitudes. The difference in signal amplitude stems from the varying spin polarization properties of respective detector electrodes, and the inverted shape of Hanle curves indicates the opposite direction of magnetization between the two detectors, as also observed in the calculated angles of 122.2° and -60.9° respectively. Indeed, when performing the spin precession experiments between contacts 2 and 3 in a straight channel, we observe a conventional Hanle curve for antiparallel orientation of electrodes. After deconvolution, the antisymmetric component is evidently zero in the straight channel, confirming the antiparallel state with $\theta = 180^\circ$. All presented results are summarized in Figure 4d showing the amplitude of symmetric and antisymmetric Hanle components as a function of the angle between detector and injector contact magnetizations present in different branches of the hexa-arm graphene spin circuit. The solid lines are the theoretical curves whereas the points correspond to the experimental data plotted at their geometry-defined angle and normalized according to eq 2.

$$\Delta R_{NL}^x = \frac{\Delta R_{NL}^x}{\sqrt{\Delta R_{NL}^{\parallel 2} + \Delta R_{NL}^{\perp 2}}} \quad (2)$$

Excellent correspondence between the geometrical device contact angles and values calculated from the measurements demonstrate the validity of the model with possible applications in complex non-collinear spin circuit designs. The studied hexa-arm architecture may be suitable for five-input weighted spin majority gate operation, where the total spin polarization in the detector circuit is determined by the individual polarizations of all the input channels while the weight of each input signal is determined by the relative orientation of injector contact magnetization with respect to the detector. Moreover, the spin polarization on inputs can be created not only via the ferromagnetic tunnel contacts, but also by spin-to-charge conversion systems based on 2D material heterostructures, or it can come from the output of another spin logic gate in a large integrated graphene spin logic circuit.
Figure 4. Non-collinear spin precession in hexa-arm architecture. a. Schematics of the hexa-arm graphene spin circuit architecture with the detector ferromagnetic contacts placed at different angles with respect to the injector ferromagnet (60°, 120°, 0°) in different graphene branches. b. Hanle spin precession curves (pink) and their deconvoluted symmetric (blue) and antisymmetric (purple) components measured in the outlined channels. c. Schematic of the angle notation used in all graphs with the black arrow representing the detector magnetization $\mathbf{M}_d$ direction and the red and blue arrows showing the injector magnetization. d. The simulated amplitude of symmetric and antisymmetric Hanle components as a function of the angle between injector/detector contacts. The points correspond to normalized experimental data obtained in different graphene branches of the hexa-arm spin circuit plotted at their geometrical angles.
Conclusion

Utilizing the efficient spin injection and accumulation in wafer-scale CVD graphene samples in complicated spin circuit architectures, we demonstrated the system capable of supporting the spin transport and precession in channel length exceeding 33 μm at room temperature. The efficient flow of spin current in the graphene channel in different geometries allows the communication of spin signals to be routed between input and output magnetic memory elements. In addition, we utilized complex graphene channel geometries of Y-junction and hexa-arm structure, where spin transport was observed simultaneously in several branches of the circuit. We show that by engineering the graphene channel geometry and orientation of spin polarization, the symmetric and antisymmetric spin precession signals can be tuned in a precise manner. The use of commercially available large-area CVD graphene grown on a Cu foil and its robustness in subsequent wafer-scale transfer and multi-step lithography process opens the route towards integrated spintronic circuits in complicated device architectures, which is one of the key requirements for industrial applications. Furthermore, the 2D transition metal dichalcogenides\textsuperscript{25–27,34,35}, magnetic materials\textsuperscript{36}, Weyl semimetals\textsuperscript{37}, and topological insulators\textsuperscript{28,29} can be integrated into van der Waals heterostructures with different branches of graphene to achieve all-electrical creation and detection of spin accumulation and the gate-controllable distribution of the pure spin current. Such independent control of spin polarization can further lead to potential applications of graphene spintronics in neuromorphic computing. Our work paves the way towards the experimental realization of graphene spin circuits where all the operations are performed only with the spin degree of freedom, which is an important milestone towards the development of spintronic logic circuits.

Methods

The CVD graphene spin circuits on highly doped Si substrate with a thermally grown 285 nm SiO\textsubscript{2} layer were patterned by electron beam lithography (EBL) and oxygen plasma etching. The large area CVD graphene (obtained from Grolltex Inc) was grown on Cu foil and transferred onto a 4-inch SiO\textsubscript{2}/Si wafer with alignment markers. Both the non-magnetic (Ti/Au) and ferromagnetic (TiO\textsubscript{2}/Co) tunnel contacts were prepared using EBL, followed by electron beam evaporation and lift-off processes. The ferromagnetic contacts were prepared by electron beam evaporation of 6 Å of Ti in two steps, each followed by in-situ oxidation in a pure oxygen atmosphere to form a TiO\textsubscript{2} tunnel barrier layer. In the same chamber, we deposited 40 nm of Co, after which the devices were finalized by liftoff in acetone at 65°C. In the measurements, a bias current was applied using a Keithley 6221 current source, and the nonlocal voltage was detected by a Keithley 2182A nanovoltmeter; the gate voltage was applied using a Keithley 2612 source meter.

Data availability

The data that support the findings of this study are available from the corresponding authors on a reasonable request.

Additional information

Acknowledgements
The authors acknowledge financial support from the European Union’s Horizon 2020 research and innovation programme under grant agreements no. 696656 and no. 785219 (Graphene Flagship Core 1 and Core 2), EU FlagEra project (from Swedish Research Council VR No. 2015-06813), Swedish Research Council VR project grants (No. 2016-03658), Graphene center and the AoA Nano program at Chalmers University of Technology.

Author information

Affiliations

1. Department of Microtechnology and Nanoscience, Chalmers University of Technology, SE-41296, Göteborg, Sweden

Contributions

DK and SPD conceived the idea and designed the experiments. DK fabricated and measured the devices. BK, AMH participated in graphene preparation. DK and SPD analyzed, interpreted the experimental data, compiled the figures and wrote the manuscript. SPD supervised and managed the research project.

Competing interests

The authors declare no competing financial interests.

Corresponding authors:

Correspondence and requests for materials should be addressed to

Dmitrii Khokhriakov, Email: dmikho@chalmers.se; Saroj P. Dash, Email: saroj.dash@chalmers.se

References


32. Gebeeyehu, Z. M. et al. Spin communication over 30 µm long channels of chemical vapor deposited graphene on SiO2. 2D Mater. 6, 34003 (2019).


SUPPLEMENTARY INFORMATION

Two-Dimensional Spintronic Circuit Architectures on Large Scale Graphene

Dmitrii Khokhriakov¹, Bogdan Karpiak¹, Anamul Md. Hoque¹, Saroj P. Dash¹

¹Department of Microtechnology and Nanoscience, Chalmers University of Technology, SE-41296, Göteborg, Sweden

Figure S1. Graphene characterization. (a) CVD Graphene channel sheet resistance $R_\square$ as a function of gate voltage $V_\text{g}$ at room temperature with 285 nm-thick SiO$_2$/n$^{++}$-Si back gate. (b) Raman spectrum of CVD graphene on SiO$_2$/n$^{++}$-Si substrate.
Figure S2. Simulated Hanle signals for different angles between injector/detector contact magnetization in a spin circuit. (a-f) Simulated Hanle signal (pink) and its symmetric (blue) and antisymmetric (purple) components for angles of 60°, 120°, 90°, -60°, -120°, 0° respectively.